

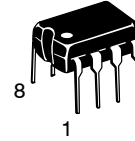
Low Offset Voltage Dual Comparators

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

The LM393 series are dual independent precision voltage comparators capable of single or split supply operation. These devices are designed to permit a common mode range-to-ground level with single supply operation. Input offset voltage specifications as low as 2.0 mV make this device an excellent selection for many applications in consumer, automotive, and industrial electronics.

Features

- Wide Single-Supply Range: 2.0 Vdc to 36 Vdc
- Split-Supply Range: ± 1.0 Vdc to ± 18 Vdc
- Very Low Current Drain Independent of Supply Voltage: 0.4 mA
- Low Input Bias Current: 25 nA
- Low Input Offset Current: 5.0 nA
- Low Input Offset Voltage: 5.0 mV (max) LM293/393
- Input Common Mode Range to Ground Level
- Differential Input Voltage Range Equal to Power Supply Voltage
- Output Voltage Compatible with DTL, ECL, TTL, MOS, and CMOS Logic Levels
- ESD Clamps on the Inputs Increase the Ruggedness of the Device without Affecting Performance
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



PDIP-8
N SUFFIX
CASE 626

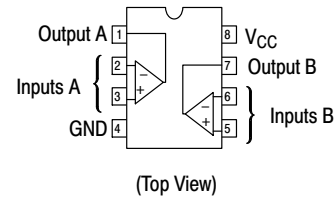


SOIC-8
D SUFFIX
CASE 751



Micro8™
DM SUFFIX
CASE 846A

PIN CONNECTIONS



DEVICE MARKING AND ORDERING INFORMATION

See detailed marking information and ordering and shipping information on page 7 of this data sheet.

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

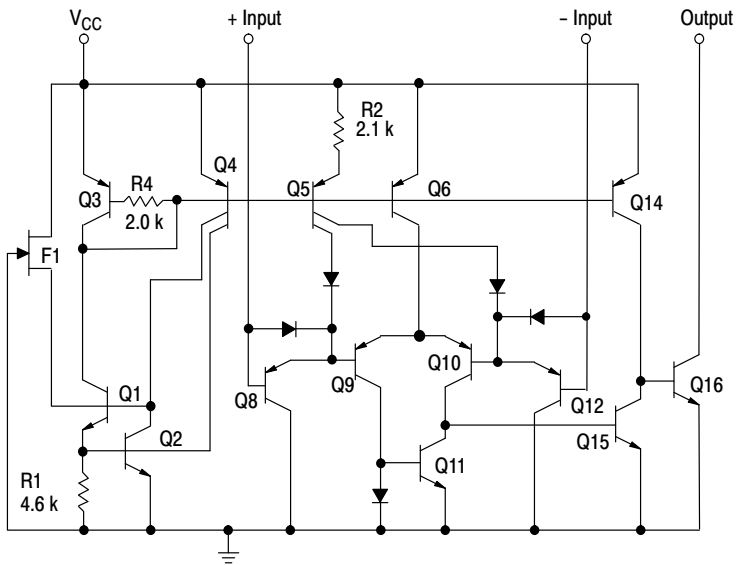


Figure 1. Representative Schematic Diagram
(Diagram shown is for 1 comparator)

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|----------------------------|--|----------------------------|
| Power Supply Voltage | V_{CC} | +36 or ± 18 | V |
| Input Differential Voltage | V_{IDR} | 36 | V |
| Input Common Mode Voltage Range | V_{ICR} | -0.3 to +36 | V |
| Output Voltage | V_O | 36 | V |
| Output Short Circuit-to-Ground Output Sink Current (Note 1) | I_{SC} I_{Sink} | Continuous 20 | mA |
| Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D $1/R_{\theta JA}$ | 570 5.7 | mW mW/ $^\circ\text{C}$ |
| Operating Ambient Temperature Range LM293 LM393, LM393E LM2903, LM2903E LM2903V, NCV2903 (Note 2) | T_A | -25 to +85 0 to +70 -40 to +105 -40 to +125 | $^\circ\text{C}$ |
| Maximum Operating Junction Temperature LM393, LM393E, LM2903, LM2903E, LM2903V LM293, NCV2903 | $T_{J(max)}$ | 150 150 | $^\circ\text{C}$ |
| Storage Temperature Range | T_{stg} | -65 to +150 | $^\circ\text{C}$ |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- The maximum output current may be as high as 20 mA, independent of the magnitude of V_{CC} , output short circuits to V_{CC} can cause excessive heating and eventual destruction.
- NCV2903 is qualified for automotive use.*

ESD RATINGS

| Rating | HBM | MM | Unit |
|--|------|-----|------|
| ESD Protection at any Pin (Human Body Model – HBM, Machine Model – MM) | | | |
| NCV2903 (Note 2) | 2000 | 200 | V |
| LM393E, LM2903E | 1500 | 150 | V |
| LM393DG/DR2G, LM2903DG/DR2G | 250 | 100 | V |
| All Other Devices | 1500 | 150 | V |

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

ELECTRICAL CHARACTERISTICS ($V_{CC} = 5.0$ Vdc, $T_{low} \leq T_A \leq T_{high}$, unless otherwise noted.)

| Characteristic | Symbol | LM293, LM393, LM393E | | | LM2903/E/V, NCV2903 | | | Unit |
|--|------------|----------------------|-----------|----------------|------------------------|-----------|----------------|---------------|
| | | Min | Typ | Max | Min | Typ | Max | |
| Input Offset Voltage (Note 4) $T_A = 25^\circ\text{C}$ $T_{low} \leq T_A \leq T_{high}$ | V_{IO} | - | ± 1.0 | ± 5.0 | - | ± 2.0 | ± 7.0 | mV |
| | | - | - | ± 9.0 | - | ± 9.0 | ± 15 | |
| Input Offset Current $T_A = 25^\circ\text{C}$ $T_{low} \leq T_A \leq T_{high}$ | I_{IO} | - | ± 5.0 | ± 50 | - | ± 5.0 | ± 50 | nA |
| | | - | - | ± 150 | - | ± 50 | ± 200 | |
| Input Bias Current (Note 5) $T_A = 25^\circ\text{C}$ $T_{low} \leq T_A \leq T_{high}$ | I_{IB} | - | 20 | 250 | - | 20 | 250 | nA |
| | | - | - | 400 | - | 20 | 500 | |
| Input Common Mode Voltage Range (Note 6) $T_A = 25^\circ\text{C}$ $T_{low} \leq T_A \leq T_{high}$ | V_{ICR} | 0 | - | $V_{CC} - 1.5$ | 0 | - | $V_{CC} - 1.5$ | V |
| | | 0 | - | $V_{CC} - 2.0$ | 0 | - | $V_{CC} - 2.0$ | |
| Voltage Gain $R_L \geq 15$ k Ω , $V_{CC} = 15$ Vdc, $T_A = 25^\circ\text{C}$ | A_{VOL} | 50 | 200 | - | 25 | 200 | - | V/mV |
| Large Signal Response Time $V_{in} =$ TTL Logic Swing, $V_{ref} = 1.4$ Vdc $V_{RL} = 5.0$ Vdc, $R_L = 5.1$ k Ω , $T_A = 25^\circ\text{C}$ | - | - | 300 | - | - | 300 | - | ns |
| Response Time (Note 7) $V_{RL} = 5.0$ Vdc, $R_L = 5.1$ k Ω , $T_A = 25^\circ\text{C}$ | t_{TLH} | - | 1.3 | - | - | 1.5 | - | μs |
| Input Differential Voltage (Note 8) All $V_{in} \geq$ GND or V^- Supply (if used) | V_{ID} | - | - | V_{CC} | - | - | V_{CC} | V |
| Output Sink Current $V_{in} \geq 1.0$ Vdc, $V_{in+} = 0$ Vdc, $V_O \leq 1.5$ Vdc $T_A = 25^\circ\text{C}$ | I_{Sink} | 6.0 | 16 | - | 6.0 | 16 | - | mA |
| Output Saturation Voltage $V_{in} \geq 1.0$ Vdc, $V_{in+} = 0$, $I_{Sink} \leq 4.0$ mA, $T_A = 25^\circ\text{C}$ $T_{low} \leq T_A \leq T_{high}$ | V_{OL} | - | 150 | 400 | - | - | 400 | mV |
| | | - | - | 700 | - | 200 | 700 | |
| Output Leakage Current $V_{in-} = 0$ V, $V_{in+} \geq 1.0$ Vdc, $V_O = 5.0$ Vdc, $T_A = 25^\circ\text{C}$ $V_{in-} = 0$ V, $V_{in+} \geq 1.0$ Vdc, $V_O = 30$ Vdc, $T_{low} \leq T_A \leq T_{high}$ | I_{OL} | - | 0.1 | - | - | 0.1 | - | nA |
| | | - | - | 1000 | - | - | 1000 | |
| Supply Current $R_L = \infty$ Both Comparators, $T_A = 25^\circ\text{C}$ $R_L = \infty$ Both Comparators, $V_{CC} = 30$ V | I_{CC} | - | 0.4 | 1.0 | - | 0.4 | 1.0 | mA |
| | | - | - | 2.5 | - | - | 2.5 | |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

LM293 $T_{low} = -25^\circ\text{C}$, $T_{high} = +85^\circ\text{C}$

LM393, LM393E $T_{low} = 0^\circ\text{C}$, $T_{high} = +70^\circ\text{C}$

LM2903, LM2903E $T_{low} = -40^\circ\text{C}$, $T_{high} = +105^\circ\text{C}$

LM2903V & NCV2903 $T_{low} = -40^\circ\text{C}$, $T_{high} = +125^\circ\text{C}$

NCV2903 is qualified for automotive use.

- The maximum output current may be as high as 20 mA, independent of the magnitude of V_{CC} , output short circuits to V_{CC} can cause excessive heating and eventual destruction.
- At output switch point, $V_O \approx 1.4$ Vdc, $R_S = 0$ Ω with V_{CC} from 5.0 Vdc to 30 Vdc, and over the full input common mode range (0 V to $V_{CC} = -1.5$ V).
- Due to the PNP transistor inputs, bias current will flow out of the inputs. This current is essentially constant, independent of the output state, therefore, no loading changes will exist on the input lines.
- Input common mode of either input should not be permitted to go more than 0.3 V negative of ground or minus supply. The upper limit of common mode range is $V_{CC} - 1.5$ V.
- Response time is specified with a 100 mV step and 5.0 mV of overdrive. With larger magnitudes of overdrive faster response times are obtainable.
- The comparator will exhibit proper output state if one of the inputs becomes greater than V_{CC} , the other input must remain within the common mode range. The low input state must not be less than -0.3 V of ground or minus supply.

LM293/393

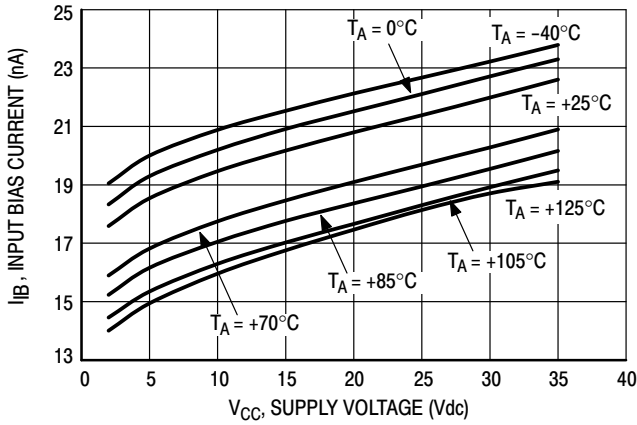


Figure 2. Input Bias Current versus Power Supply Voltage

LM2903

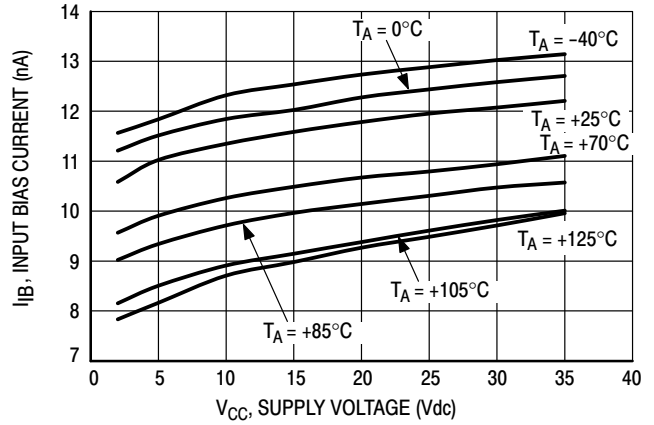


Figure 3. Input Bias Current versus Power Supply Voltage

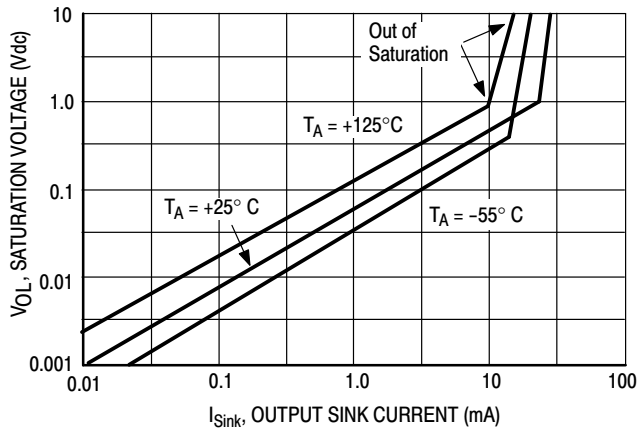


Figure 4. Output Saturation Voltage versus Output Sink Current

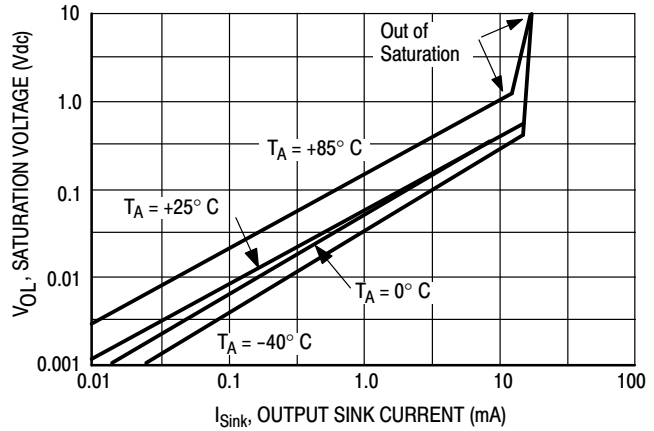


Figure 5. Output Saturation Voltage versus Output Sink Current

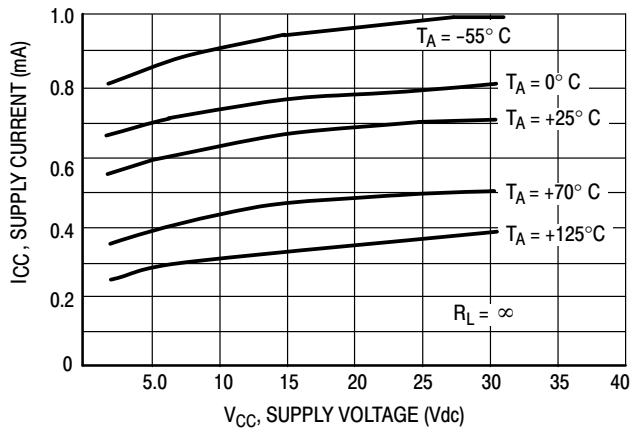


Figure 6. Power Supply Current versus Power Supply Voltage

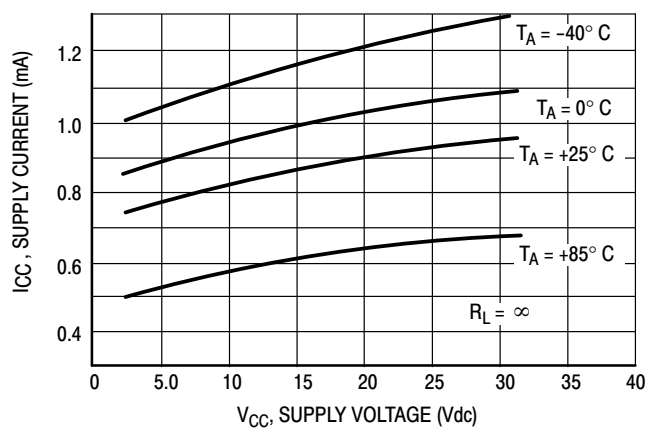
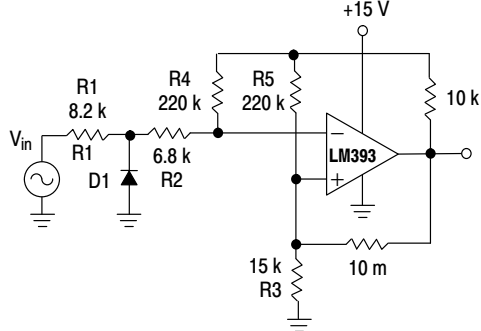


Figure 7. Power Supply Current versus Power Supply Voltage

APPLICATIONS INFORMATION

These dual comparators feature high gain, wide bandwidth characteristics. This gives the device oscillation tendencies if the outputs are capacitively coupled to the inputs via stray capacitance. This oscillation manifests itself during output transitions (V_{OL} to V_{OH}). To alleviate this situation, input resistors $< 10\text{ k}\Omega$ should be used.



D1 prevents input from going negative by more than 0.6 V.

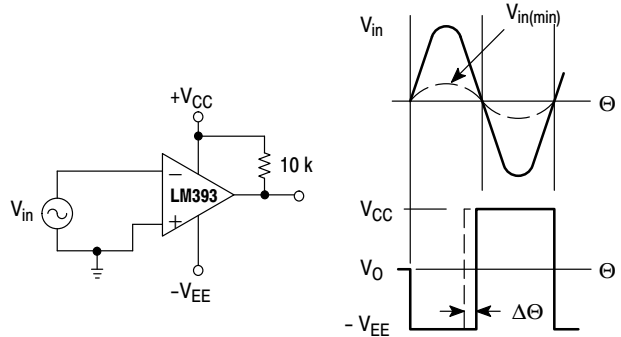
$$R1 + R2 = R3$$

$$R3 \leq \frac{R5}{10} \text{ for small error in zero crossing.}$$

Figure 8. Zero Crossing Detector (Single Supply)

The addition of positive feedback ($< 10\text{ mV}$) is also recommended. It is good design practice to ground all unused pins.

Differential input voltages may be larger than supply voltage without damaging the comparator's inputs. Voltages more negative than -0.3 V should not be used.



$$V_{in(min)} \approx 0.4\text{ V peak for } 1\% \text{ phase distortion } (\Delta\Theta).$$

Figure 9. Zero Crossing Detector (Split Supply)

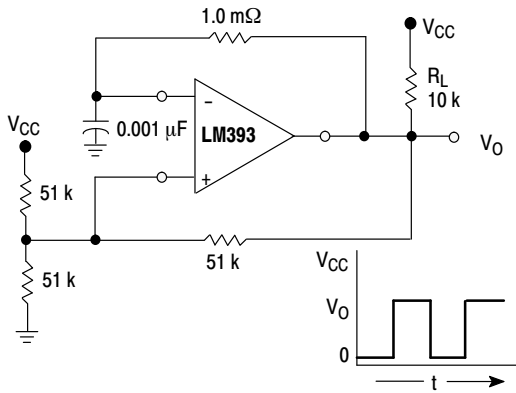
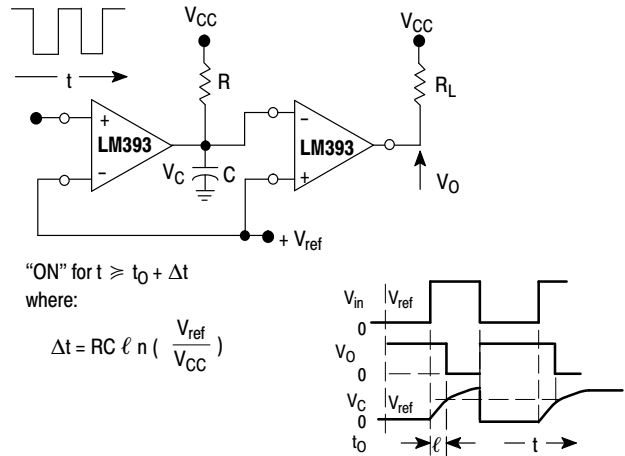


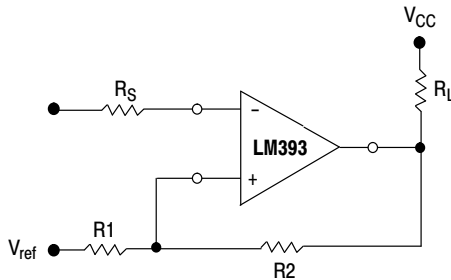
Figure 10. Free-Running Square-Wave Oscillator



"ON" for $t \geq t_0 + \Delta t$
where:

$$\Delta t = RC \ell n \left(\frac{V_{ref}}{V_{CC}} \right)$$

Figure 11. Time Delay Generator



$$R_S = R1 \parallel R2$$

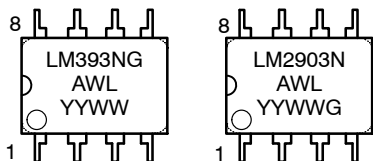
$$V_{th1} = V_{ref} + \frac{(V_{CC} - V_{ref}) R1}{R1 + R2 + R_L}$$

$$V_{th2} = V_{ref} - \frac{(V_{ref} - V_{O\text{ Low}}) R1}{R1 + R2}$$

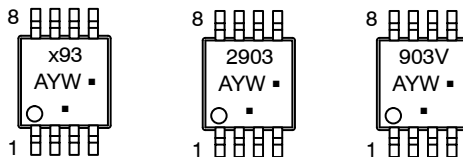
Figure 12. Comparator with Hysteresis

MARKING DIAGRAMS

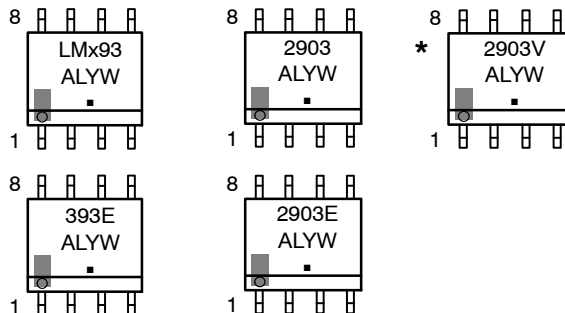
PDIP-8
CASE 626



Micro8
CASE 846A



SOIC-8
CASE 751



- x = 2 or 3
- A = Assembly Location
- WL, L = Wafer Lot
- YY, Y = Year
- WW, W = Work Week
- , G = Pb-Free Package

(Note: Microdot may be in either location)

*This marking diagram also applies to NCV2903DR2G

LM393, LM393E, LM293, LM2903, LM2903E, LM2903V, NCV2903

ORDERING INFORMATION

| Device | Operating Temperature Range | Package | Shipping [†] |
|---------------|-----------------------------|---------------------|-----------------------|
| LM293DG | -25°C to +85°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| LM293DR2G | | | 2500 / Tape & Reel |
| LM293DMR2G | | Micro8 (Pb-Free) | 4000 / Tape and Reel |
| LM393DG | 0°C to +70°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| LM393DR2G | | | 2500 / Tape & Reel |
| LM393EDR2G | | SOIC-8 (Pb-Free) | 2500 / Tape & Reel |
| LM393NG | | PDIP-8 (Pb-Free) | 50 Units / Rail |
| LM393DMR2G | | Micro8 (Pb-Free) | 4000 / Tape and Reel |
| LM2903DG | -40°C to +105°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| LM2903DR2G | | | 2500 / Tape & Reel |
| LM2903EDR2G | | SOIC-8 (Pb-Free) | 2500 / Tape & Reel |
| LM2903DMR2G | | Micro8 (Pb-Free) | 4000 / Tape and Reel |
| LM2903NG | | PDIP-8 (Pb-Free) | 50 Units / Rail |
| LM2903VDG | -40°C to +125°C | SOIC-8 (Pb-Free) | 98 Units / Rail |
| LM2903VDR2G | | | 2500 / Tape & Reel |
| LM2903VNG | | PDIP-8 (Pb-Free) | 50 Units / Rail |
| NCV2903DR2G* | | SOIC-8 (Pb-Free) | 2500 / Tape & Reel |
| NCV2903DMR2G* | | Micro8 (Pb-Free) | 4000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

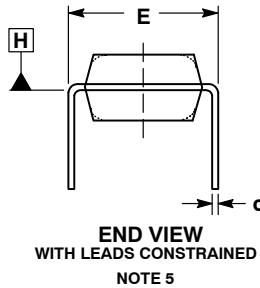
ON Semiconductor®



SCALE 1:1

PDIP-8
CASE 626-05
ISSUE P

DATE 22 APR 2015



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. DIMENSIONS A, A1 AND L ARE MEASURED WITH THE PACKAGE SEATED IN JEDEC SEATING PLANE GAUGE GS-3.
4. DIMENSIONS D, D1 AND E1 DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS. MOLD FLASH OR PROTRUSIONS ARE NOT TO EXCEED 0.10 INCH.
5. DIMENSION E IS MEASURED AT A POINT 0.015 BELOW DATUM PLANE H WITH THE LEADS CONSTRAINED PERPENDICULAR TO DATUM C.
6. DIMENSION eB IS MEASURED AT THE LEAD TIPS WITH THE LEADS UNCONSTRAINED.
7. DATUM PLANE H IS COINCIDENT WITH THE BOTTOM OF THE LEADS, WHERE THE LEADS EXIT THE BODY.
8. PACKAGE CONTOUR IS OPTIONAL (ROUNDED OR SQUARE CORNERS).

| DIM | INCHES | | MILLIMETERS | |
|-----|-----------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | ---- | 0.210 | ---- | 5.33 |
| A1 | 0.015 | ---- | 0.38 | ---- |
| A2 | 0.115 | 0.195 | 2.92 | 4.95 |
| b | 0.014 | 0.022 | 0.35 | 0.56 |
| b2 | 0.060 TYP | | 1.52 TYP | |
| C | 0.008 | 0.014 | 0.20 | 0.36 |
| D | 0.355 | 0.400 | 9.02 | 10.16 |
| D1 | 0.005 | ---- | 0.13 | ---- |
| E | 0.300 | 0.325 | 7.62 | 8.26 |
| E1 | 0.240 | 0.280 | 6.10 | 7.11 |
| e | 0.100 BSC | | 2.54 BSC | |
| eB | ---- | 0.430 | ---- | 10.92 |
| L | 0.115 | 0.150 | 2.92 | 3.81 |
| M | ---- | 10° | ---- | 10° |

GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- YY = Year
- WW = Work Week
- G = Pb-Free Package

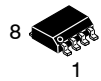
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- STYLE 1:
PIN 1. AC IN
2. DC + IN
3. DC - IN
4. AC IN
5. GROUND
6. OUTPUT
7. AUXILIARY
8. V_{CC}

| | | |
|------------------|-------------|--|
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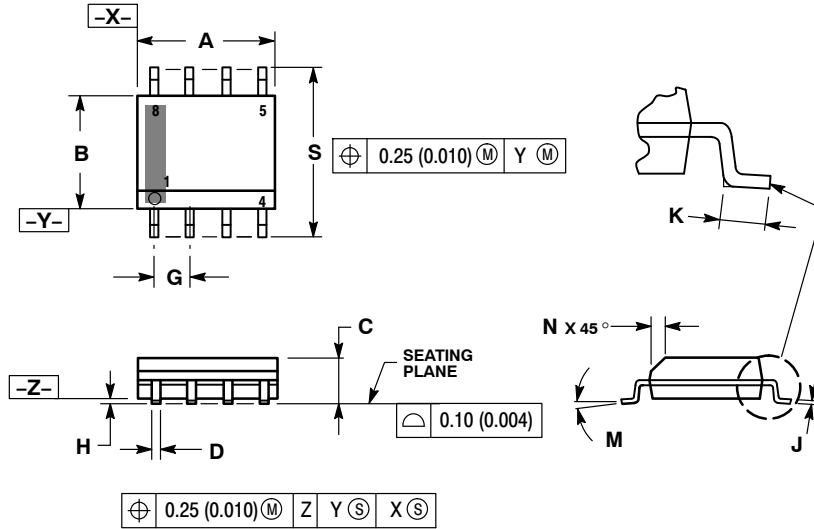
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

SOIC-8 NB
CASE 751-07
ISSUE AK

DATE 16 FEB 2011



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

| DIM | MILLIMETERS | | INCHES | |
|-----|-------------|------|-----------|-------|
| | MIN | MAX | MIN | MAX |
| A | 4.80 | 5.00 | 0.189 | 0.197 |
| B | 3.80 | 4.00 | 0.150 | 0.157 |
| C | 1.35 | 1.75 | 0.053 | 0.069 |
| D | 0.33 | 0.51 | 0.013 | 0.020 |
| G | 1.27 BSC | | 0.050 BSC | |
| H | 0.10 | 0.25 | 0.004 | 0.010 |
| J | 0.19 | 0.25 | 0.007 | 0.010 |
| K | 0.40 | 1.27 | 0.016 | 0.050 |
| M | 0° | 8° | 0° | 8° |
| N | 0.25 | 0.50 | 0.010 | 0.020 |
| S | 5.80 | 6.20 | 0.228 | 0.244 |

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXXX = Specific Device Code
A = Assembly Location
L = Wafer Lot
Y = Year
W = Work Week
▪ = Pb-Free Package

XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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CASE 751-07
ISSUE AK

DATE 16 FEB 2011

- | | | | |
|--|---|---|---|
| <p>STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER</p> | <p>STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1</p> | <p>STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1</p> | <p>STYLE 4: PIN 1. ANODE 2. ANODE 3. ANODE 4. ANODE 5. ANODE 6. ANODE 7. ANODE 8. COMMON CATHODE</p> |
| <p>STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE</p> | <p>STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE</p> | <p>STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd</p> | <p>STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1</p> |
| <p>STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON</p> | <p>STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND</p> | <p>STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1</p> | <p>STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> | <p>STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN</p> | <p>STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON</p> | <p>STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1</p> |
| <p>STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC</p> | <p>STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE</p> | <p>STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1</p> | <p>STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN</p> |
| <p>STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6</p> | <p>STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND</p> | <p>STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT</p> | <p>STYLE 24: PIN 1. BASE 2. EMITTER 3. COLLECTOR/ANODE 4. COLLECTOR/ANODE 5. CATHODE 6. CATHODE 7. COLLECTOR/ANODE 8. COLLECTOR/ANODE</p> |
| <p>STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT</p> | <p>STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC</p> | <p>STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN</p> | <p>STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN</p> |
| <p>STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1</p> | <p>STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1</p> | | |

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| DESCRIPTION: | SOIC-8 NB | PAGE 2 OF 2 |

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MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 2:1

Micro8 CASE 846A-02 ISSUE K

DATE 16 JUL 2020



TOP VIEW

NOTE 3



SIDE VIEW



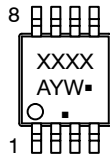
END VIEW

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSION *b* DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.10 mm IN EXCESS OF MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS *D* AND *E* DO NOT INCLUDE MOLD FLASH, PROTRUSION OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 mm PER SIDE. DIMENSION *E* DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 mm PER SIDE. DIMENSIONS *D* AND *E* ARE DETERMINED AT DATUM *F*.
5. DATUMS *A* AND *B* ARE TO BE DETERMINED AT DATUM *F*.
6. *A1* IS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

$\phi 0.08$ (0.003) M C B S A S

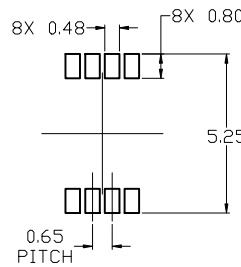
GENERIC MARKING DIAGRAM*



- XXXX = Specific Device Code
- A = Assembly Location
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERM/D.

| DIM | MILLIMETERS | | |
|----------------|-------------|------|------|
| | MIN. | NOM. | MAX. |
| A | --- | --- | 1.10 |
| A1 | 0.05 | 0.08 | 0.15 |
| b | 0.25 | 0.33 | 0.40 |
| c | 0.13 | 0.18 | 0.23 |
| D | 2.90 | 3.00 | 3.10 |
| E | 2.90 | 3.00 | 3.10 |
| e | 0.65 BSC | | |
| H _E | 4.75 | 4.90 | 5.05 |
| L | 0.40 | 0.55 | 0.70 |

STYLE 1:

1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN
6. DRAIN
7. DRAIN
8. DRAIN

STYLE 2:

1. SOURCE 1
2. GATE 1
3. SOURCE 2
4. GATE 2
5. DRAIN 2
6. DRAIN 2
7. DRAIN 1
8. DRAIN 1

STYLE 3:

1. N-SOURCE
2. N-GATE
3. P-SOURCE
4. P-GATE
5. P-DRAIN
6. P-DRAIN
7. N-DRAIN
8. N-DRAIN

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